APPENDIX-F

Specification for 6 items for use in P.A. of 200 kw NAUTEL DRM Transmitter

Sr.no.	Name of component	Part no	specification	OEM	quantity	remarks
1	MOSFET	APT50M50JFLL	1. Device:N-channel power MOSFET Through Hole, 2.drain source voltage(VDS):500V 3.Contineous Drain Current(ID):71A@TC=25°C 4.RDS(on) :0.050 ohm 5.Gate-Source voltage :±30 V contineous 6.Pulsed Drain Current : 284A 7.Total Power Dissipation:595w@TC=25°C 8.Junction Temp.:-55°C to +150 °C Package : SOT-227 /ISOTOP 9.Body Diode :Fast Recovery Body Diode	Microchip Technology/APT	100	
2	MOSFET	IXFH30N50P	1.N-channel Power MOSFET Through Hole 2.Drain-Source Voltage (VDSS):500V 3.Contineous Drain Current(ID25):30A@TC=25°C 4.RDS(on):<200 milliohm 5.Contineous Gate Source Voltage(VGSS): ±30V 6.Pulse Drain Current(IDM) :75A 7.Total Power Dissipation (PD):460W@TC=25°C 8.Junction Temp. :-55°C to +150°C 9.Package : TO-247AD(IXFH) intrinsic diode:Fast intrinsic diode	IXYS(now Little fuse)	75	
3	RESISTOR	RK73H2BL1001F	1.1 kΩ (1001 marking) 2.tolerance ±1% 3.power rating ¼ W 4.Technology Metal film/thick-film SMD ,as per OEM construction 5.mounting surface mounting 6.compliance RoHS compliant	KOA Speer Electronics	100	
4	RESISTOR	RK73H2BL1004F	1.Mounting - SMT/chip resistor 2.Resistance – 1MΩ 3.Tolerance - ±1% 4.Rated Power – ¼ W 5.Type – metal film/fixed film chip resistor 6.compliance – Rohs compliant	KOA Speer Electronics	100	

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5	RESISTOR	CR2512-2W-2-0R0FT-W	1.Resistance - 20Ω 2.Rated Power – 2 W 3.Tolerance - ±1% 4.Package/Size - 2512/chip 5.Technology – thick film/Metal Glaze 6.Mounting – SMD/SMT 7.Working Voltage -200 v 8.TCR -100 ppm/°C 9.Operating Temp. -- -55°C to +155°C 10.RoHS –Compliant 11.Termination –Matte Tin/Nickel Barrier 12.Packing – Original manufacturer packing 13.Make --- VENKEL		100	
6	RESISTOR	HPC-125	1.Rated Power – 5W 2.Resistance value --5Ω 3.Tolerance -- ±1% 4. Technology – High Power/Wire Wound or equivalent 5. Mounting –Axial/ as per OEM design 6.Op. Temp. – Manufacturer Standard 7.Construction – Flame-retardant,robust industrial construction 8.Make –OEM/reputed equivalent	----------	100	
	MOSFET	MOSFET 1.docx	Data Sheet of MOSFET IXFH30N50P			
	MOSFET	MOSFET 2.docx	Data sheet of MOSFET APT50M50JFLL			

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